

600V N-Channel Power MOSFET



TO-252

TO-251

23

Pin Definition:
1. Gate
2. Drain
3. Source

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)
600	12 @ V _{GS} =10V	1

General Description

The TSM1N60L is used an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain- to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

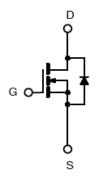
Features

- Robust high voltage termination
- Avalanche energy specified
- Diode is characterized for use in bridge circuits
- Source to Drain diode recovery time comparable to a discrete fast recovery diode.
- I_{DSS} and V_{DS(on)} specified at elevated temperature

Ordering Information

Part No.	Package	Packing
TSM1N60LCP RO	TO-252	2.5Kpcs / 13" Reel
TSM1N60LCH C5	TO-251	50pcs / Tube

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	600	V	
Gate-Source Voltage	V_{GS}	±30	V	
Continuous Drain Current	I _D	1	Α	
Pulsed Drain Current	I _{DM}	4	А	
Continuous Source Current (Diode Conduction) ^{a,b}	I _S	1	Α	
Single Pulse Drain to Source Avalanche Energy	EAC	20	1	
$(V_{DD} = 100V, V_{GS}=10V, I_{AS}=2A, L=10mH, R_{G}=25\Omega)$	EAS	20	mJ	
Maximum Power Dissipation @Ta = 25 °C	P_{D}	2.5	W	
Operating Junction Temperature	TJ	+150	°C	
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	







Thermal Performance

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	T_L	10	S
Thermal Resistance - Junction to Ambient	RO _{JA}	62.5	°C/W

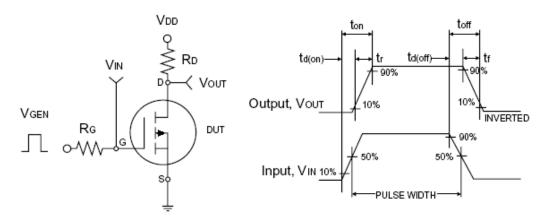
Notes: Surface mounted on FR4 board t ≤ 10sec

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	600			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 0.6A$	R _{DS(ON)}		10.5	12	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	2.0		4.0	V
Zero Gate Voltage Drain Current	$V_{DS} = 600 V, V_{GS} = 0 V$	I _{DSS}			10	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			± 100	nA
Forward Transconductance	$V_{DS} \ge 50 V$, $I_D = 0.5 A$	g _{fs}		10		S
Diode Forward Voltage	$I_{S} = 1A, V_{GS} = 0V$	V_{SD}			1.5	V
Dynamic ^b						
Total Gate Charge	\/ - 400\/ - 10	Q_g		8.5	14	
Gate-Source Charge	$V_{DS} = 400V, I_{D} = 1A,$ $V_{GS} = 10V$	Q_gs		1.8		nC
Gate-Drain Charge	V _{GS} = 10 V	Q_{gd}		4		
Input Capacitance	\/ - 25\/ \/ - 0\/	C_{iss}		210		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ - f = 1.0MHz	Coss		28		pF
Reverse Transfer Capacitance	1 - 1.01VII 12	C_{rss}		4.2		
Switching ^c						
Turn-On Delay Time	$V_{GS} = 10V, I_D = 1A,$ $V_{DS} = 300V, R_G = 6\Omega$	t _{d(on)}		8		
Turn-On Rise Time		t _r		21		nS
Turn-Off Delay Time		t _{d(off)}		18		
Turn-Off Fall Time		t _f		24		

Notes:

- a. Pulse test: pulse width <=300uS, duty cycle <=2%
- b. For design reference only, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.



Switching Test Circuit

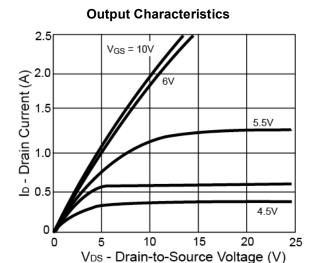
Switchin Waveforms



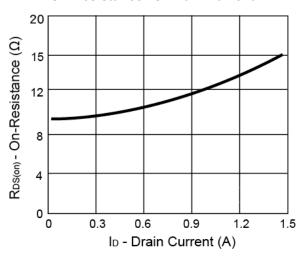
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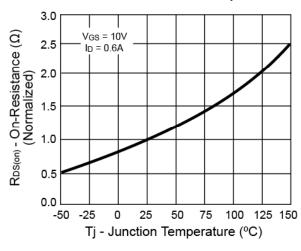
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



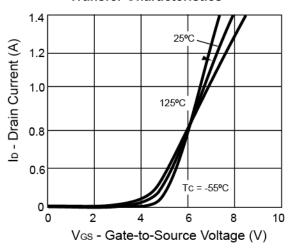
On-Resistance vs. Drain Current



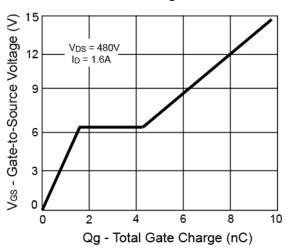
On-Resistance vs. Junction Temperature



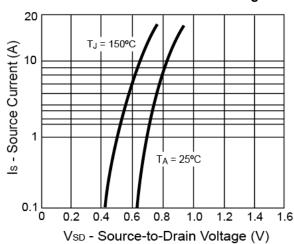
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



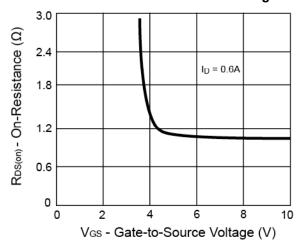


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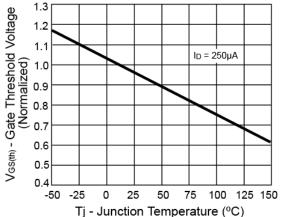


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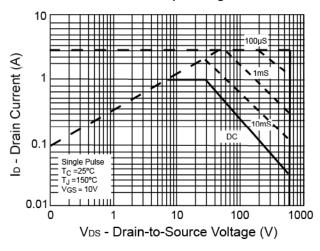
On-Resistance vs. Gate-Source Voltage



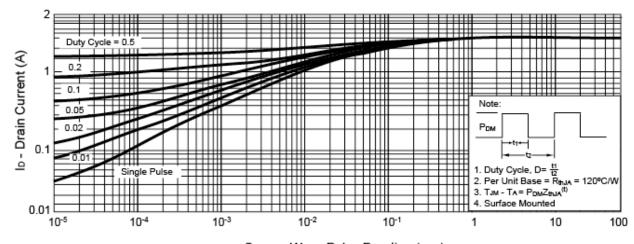
Threshold Voltage



Maximum Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

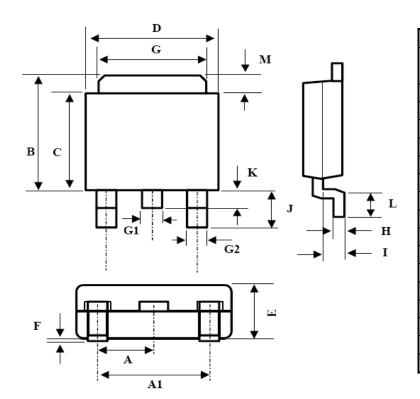






600V N-Channel Power MOSFET

SOT-252 Mechanical Drawing



TO-252 DIMENSION					
DIM	MILLIMETERS		INCHES		
ווועו	MIN	MAX	MIN	MAX	
Α	2.3E	3SC	0.09	BSC	
A1	4.6E	BSC	0.18	BSC	
В	6.80	7.20	0.268	0.283	
C	5.40	5.60	0.213	0.220	
D	6.40	6.65	0.252	0.262	
Е	2.20	2.40	0.087	0.094	
F	0.00	0.20	0.000	0.008	
G	5.20	5.40	0.205	0.213	
G1	0.75	0.85	0.030	0.033	
G2	0.55	0.65	0.022	0.026	
Н	0.35	0.65	0.014	0.026	
	0.90	1.50	0.035	0.059	
J	2.20	2.80	0.087	0.110	
K	0.50	1.10	0.020	0.043	
L	0.90	1.50	0.035	0.059	
М	1.30	1.70	0.051	0.67	

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

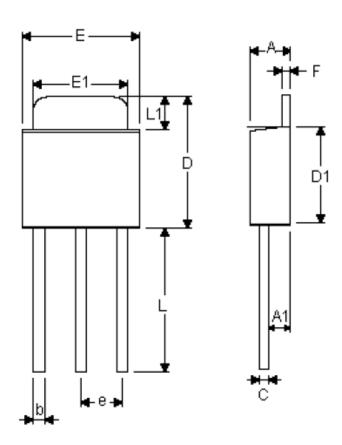
L = Lot Code







SOT-251 Mechanical Drawing



TO-251 DIMENSION					
DIM	MILLIMETERS		INCHES		
ואווט	MIN	MAX	MIN	MAX	
Α	2.20	2.4	0.087	0.095	
A1	1.10	1.30	0.043	0.051	
b	0.40	0.80	0.016	0.032	
С	0.40	0.60	0.016	0.024	
D	6.70	7.30	0.264	0.287	
D1	5.40	5.65	0.213	0.222	
Е	6.40	6.65	0.252	0.262	
е	2.10	2.50	0.083	0.098	
F	0.40	0.60	0.016	0.024	
L	7.00	8.00	0.276	0.315	
L1	1.60	1.86	0.063	0.073	

Marking Diagram



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1–3ep, **3**–3ct, **K**

L = Lot Code



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